



# SPP3413

## P-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPP3413 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

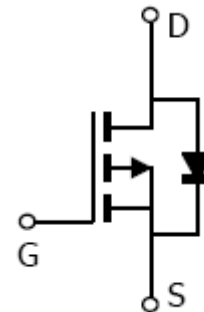
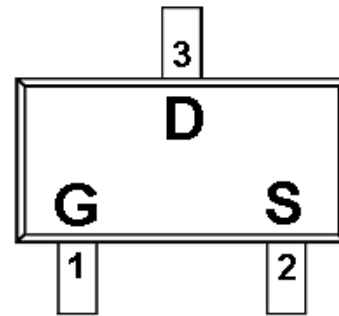
### FEATURES

- ◆ -20V/-3.4A, $R_{DS(ON)}=95m\Omega@V_{GS}=-4.5V$
- ◆ -20V/-2.4A, $R_{DS(ON)}=120m\Omega@V_{GS}=-2.5V$
- ◆ -20V/-1.7A, $R_{DS(ON)}=145m\Omega@V_{GS}=-1.8V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23-3L package design

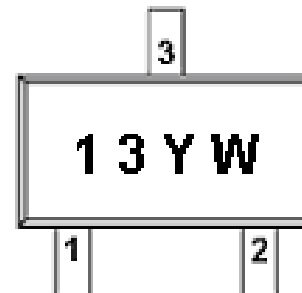
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION(SOT-23-3L)



### PART MARKING



Y : Year Code  
W : Week Code



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### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3413S23RGB	SOT-23-3L	13

- ※ Week Code : A ~ Z( 1 ~ 26 ) ; a ~ z( 27 ~ 52 )
- ※ SPP3413S23RGB : Tape Reel ; Pb – Free ; Halogen – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	-20	V	
Gate –Source Voltage	V <sub>GSS</sub>	±12	V	
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	TA=25°C	-3.5	A
		TA=70°C	-2.8	
Pulsed Drain Current	I <sub>DM</sub>	-15	A	
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.4	A	
Power Dissipation	P <sub>D</sub>	TA=25°C	1.25	W
		TA=70°C	0.8	
Operating Junction Temperature	T <sub>J</sub>	-55/150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C	
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	105	°C/W	



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### ELECTRICAL CHARACTERISTICS

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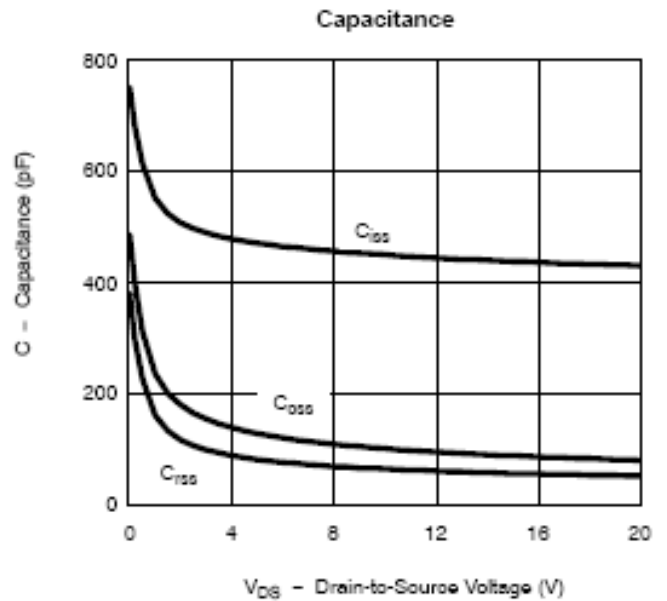
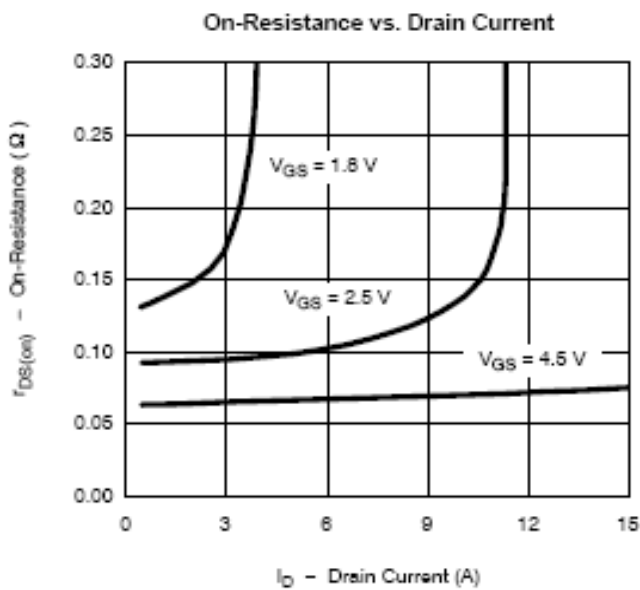
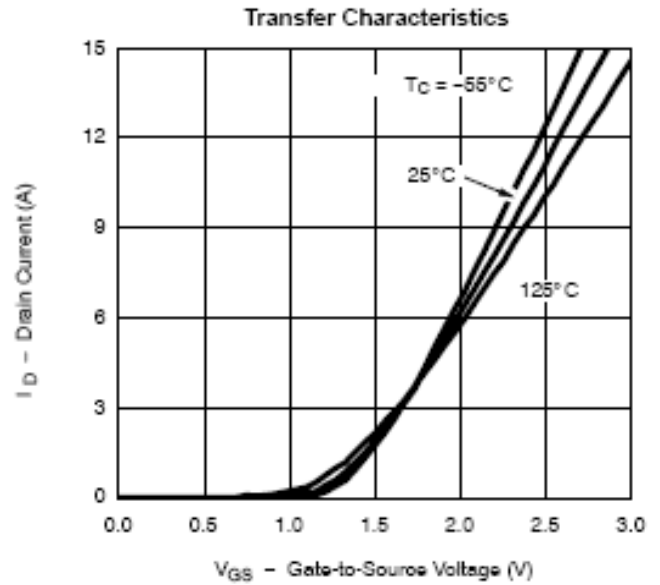
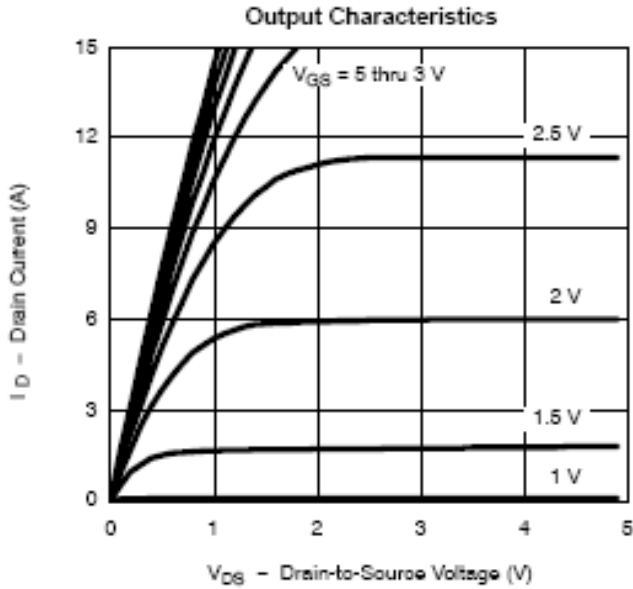
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35		-0.8	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$			-1	uA
		$V_{DS}=-20V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-4.5V$	-6			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-3.4A$		0.076	0.095	$\Omega$
		$V_{GS}=-2.5V, I_D=-2.4A$		0.097	0.120	
		$V_{GS}=-1.8V, I_D=-1.7A$		0.123	0.145	
Forward Transconductance	$g_{fs}$	$V_{DS}=-5V, I_D=-2.8A$		6		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.5A, V_{GS}=0V$		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-6V, V_{GS}=-4.5V$ $I_D=-2.8A$		4.8	8	nC
Gate-Source Charge	$Q_{gs}$			1.0		
Gate-Drain Charge	$Q_{gd}$			1.0		
Input Capacitance	$C_{iss}$	$V_{DS}=-6V, V_{GS}=0V$ $f=1MHz$		485		pF
Output Capacitance	$C_{oss}$			85		
Reverse Transfer Capacitance	$C_{rss}$			40		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-6V, R_L=6\Omega$ $I_D=-1.0A, V_{GEN}=-4.5V$ $R_G=6\Omega$		10	16	nS
	$t_r$			13	23	
Turn-Off Time	$t_{d(off)}$			18	25	
	$t_f$			15	20	



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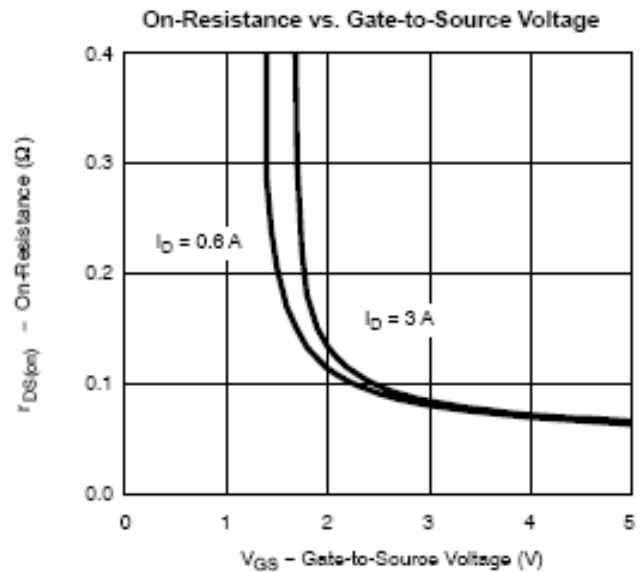
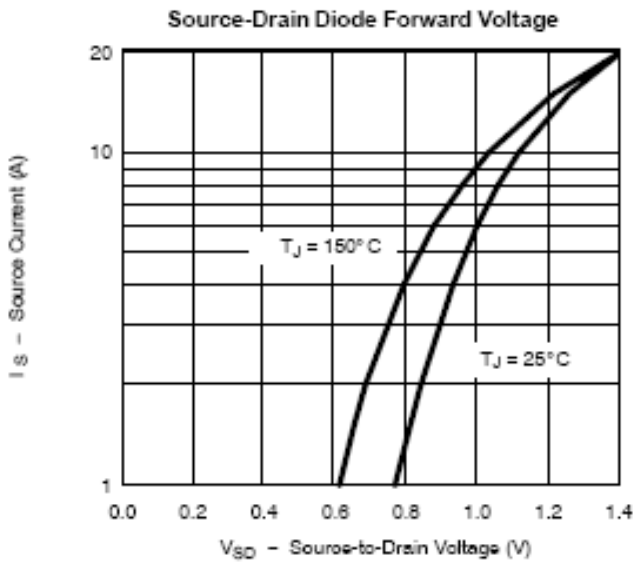
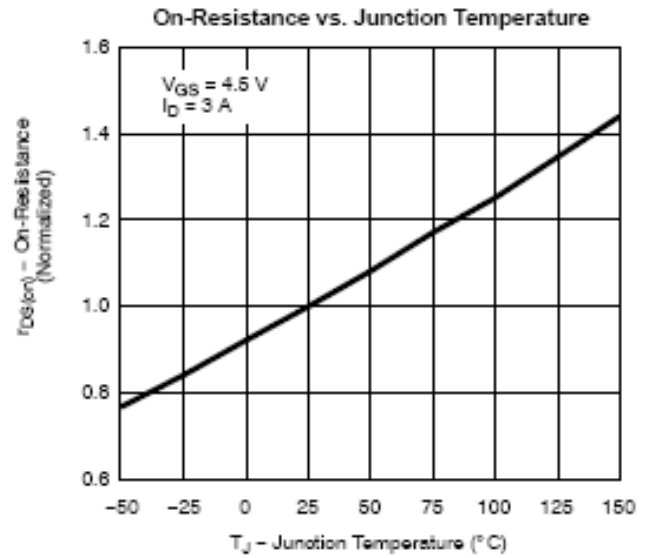
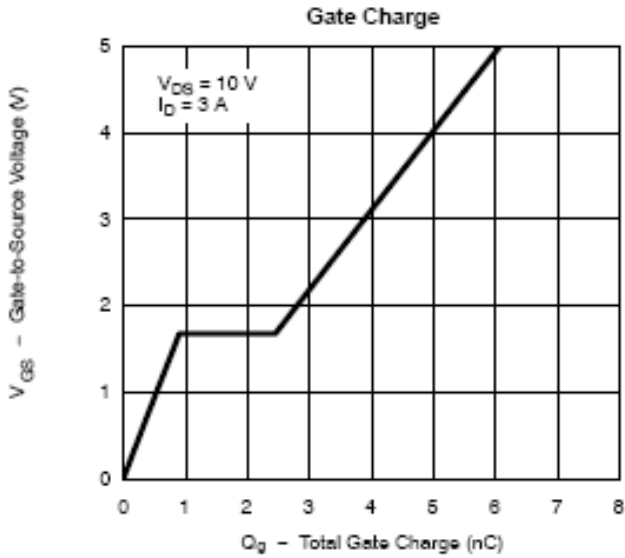
### TYPICAL CHARACTERISTICS





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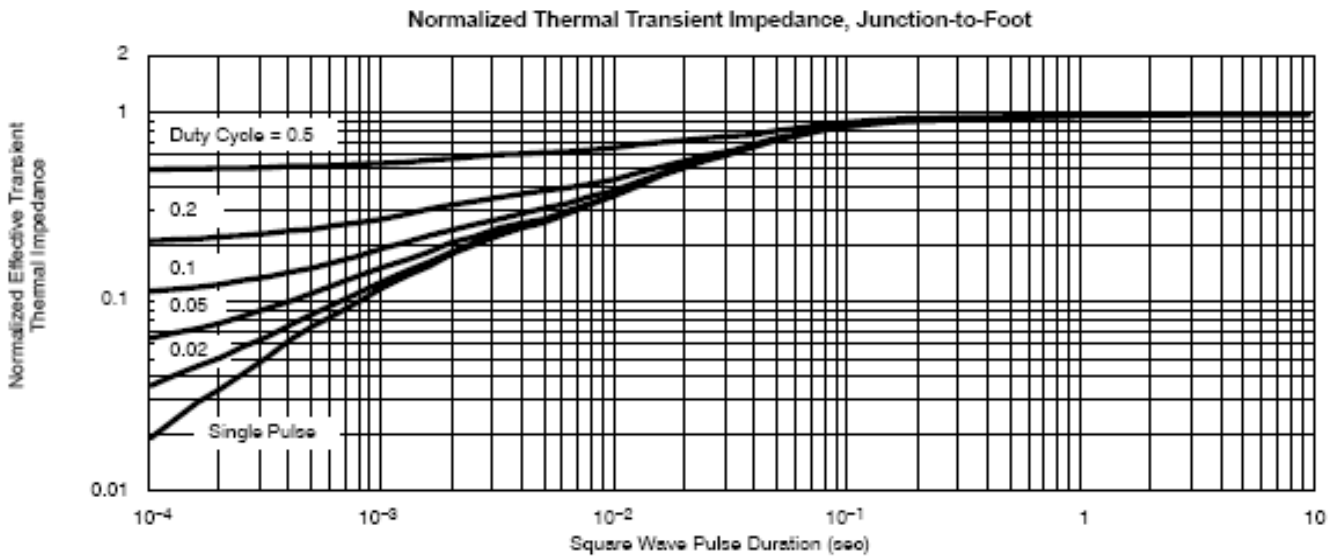
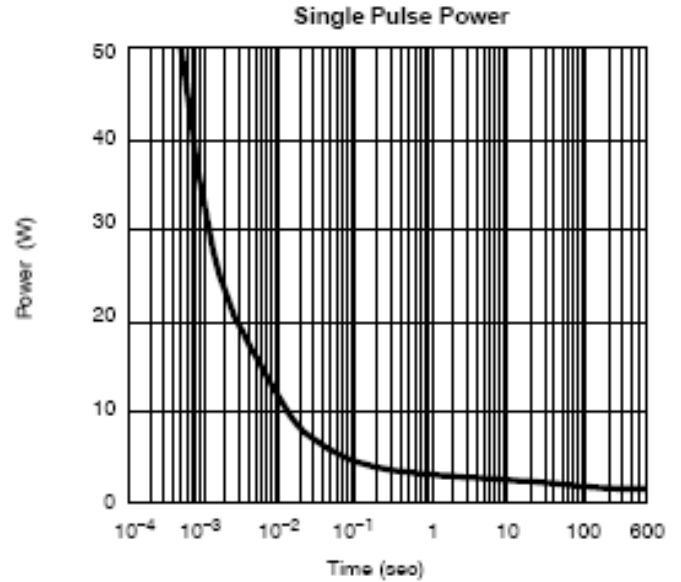
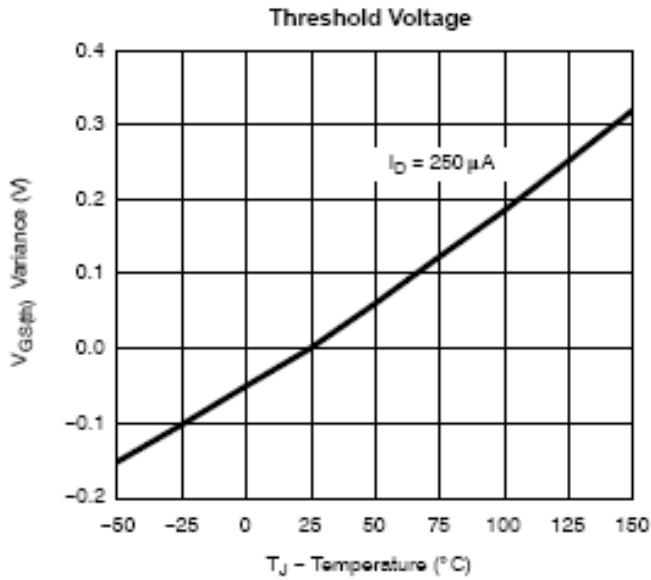
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